

1 Scope

The present specifications shall apply to an SJPL-F4.

2 Outline

Type	Silicon Diode
Structure	Resin Molded
Applications	High Frequency Rectification

3 Flammability

UL94V-0(Equivalent)

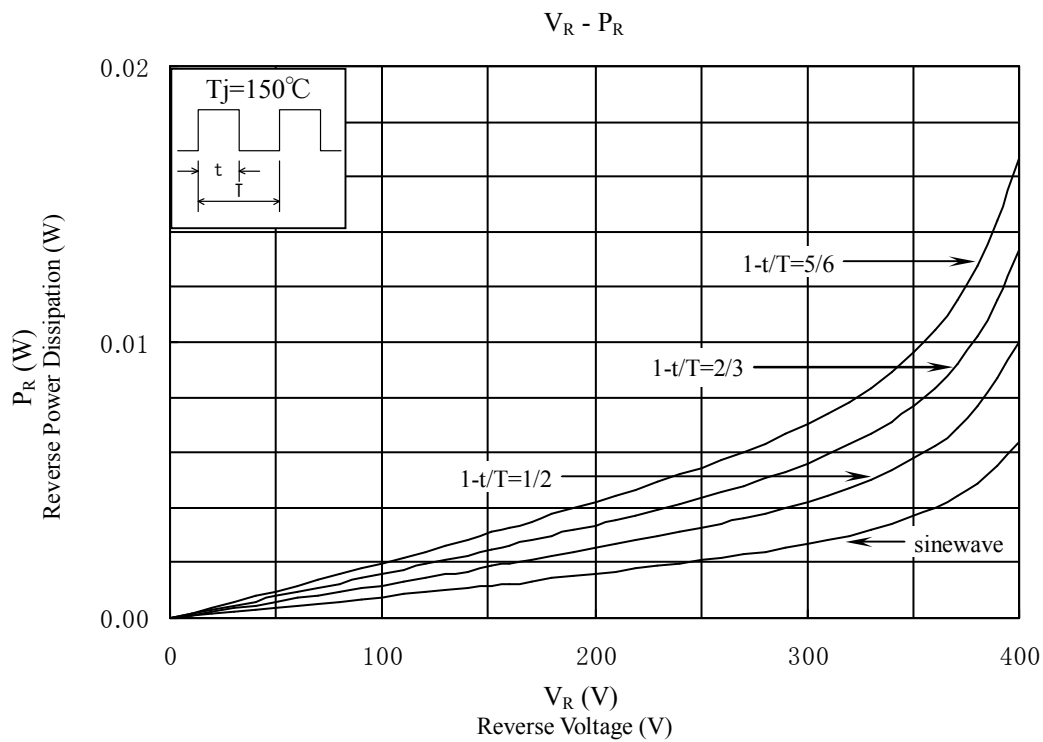
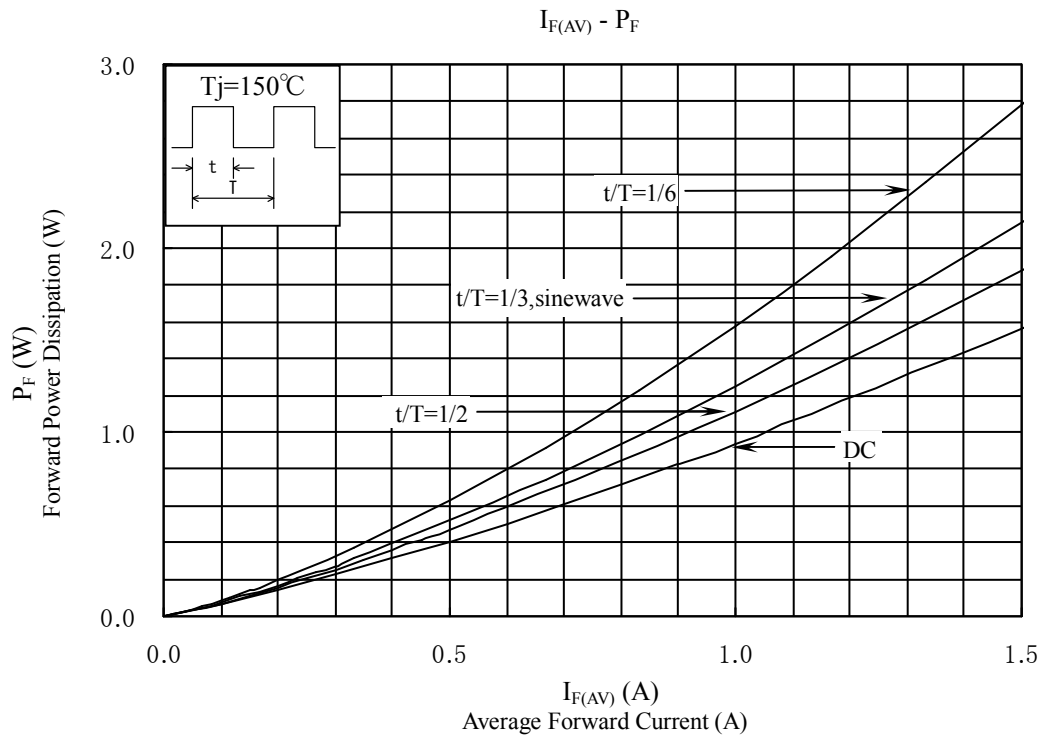
4 Absolute maximum ratings

No.	Item	Symbol	Unit	Rating	Conditions
1	Transient Peak Reverse Voltage	V_{RSM}	V	400	
2	Peak Reverse Voltage	V_{RM}	V	400	
3	Average Forward Current	$I_{F(AV)}$	A	1.5	Refer to Derating of 7
4	Peak Surge Forward Current	I_{FSM}	A	25	10msec. Half sinewave, one shot
5	I^2t Limiting Value	I^2t	A^2s	3.125	$1msec \leq t \leq 10msec$
6	Junction Temperature	T_j	$^{\circ}C$	-40~+150	
7	Storage Temperature	T_{stg}	$^{\circ}C$	-40~+150	

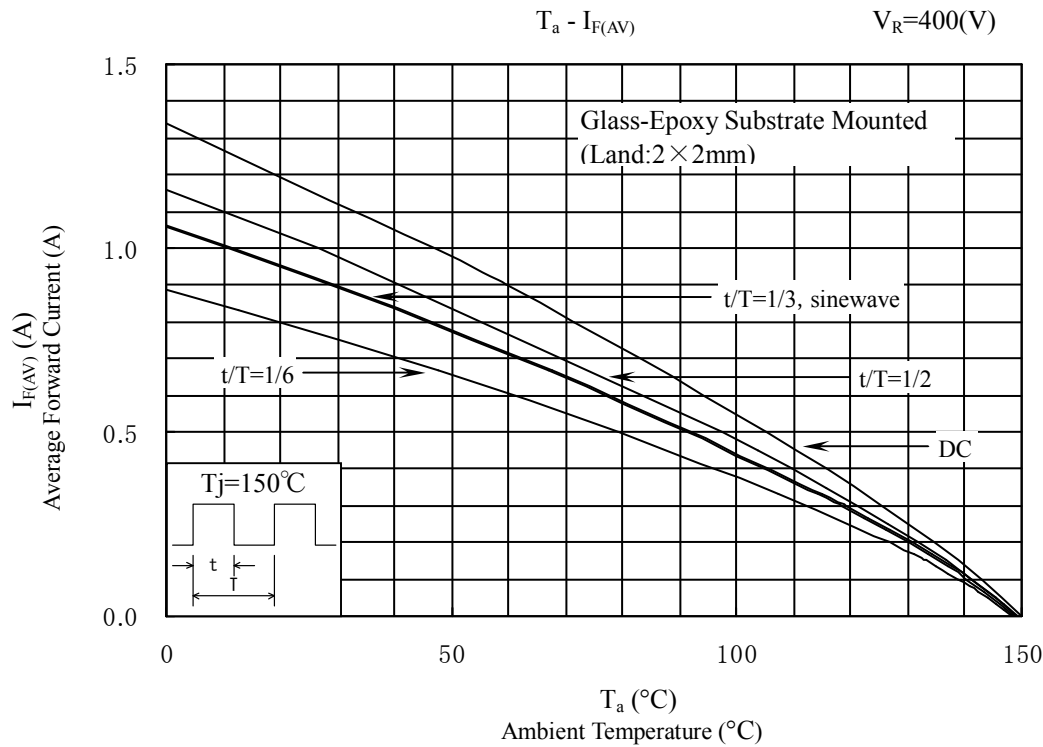
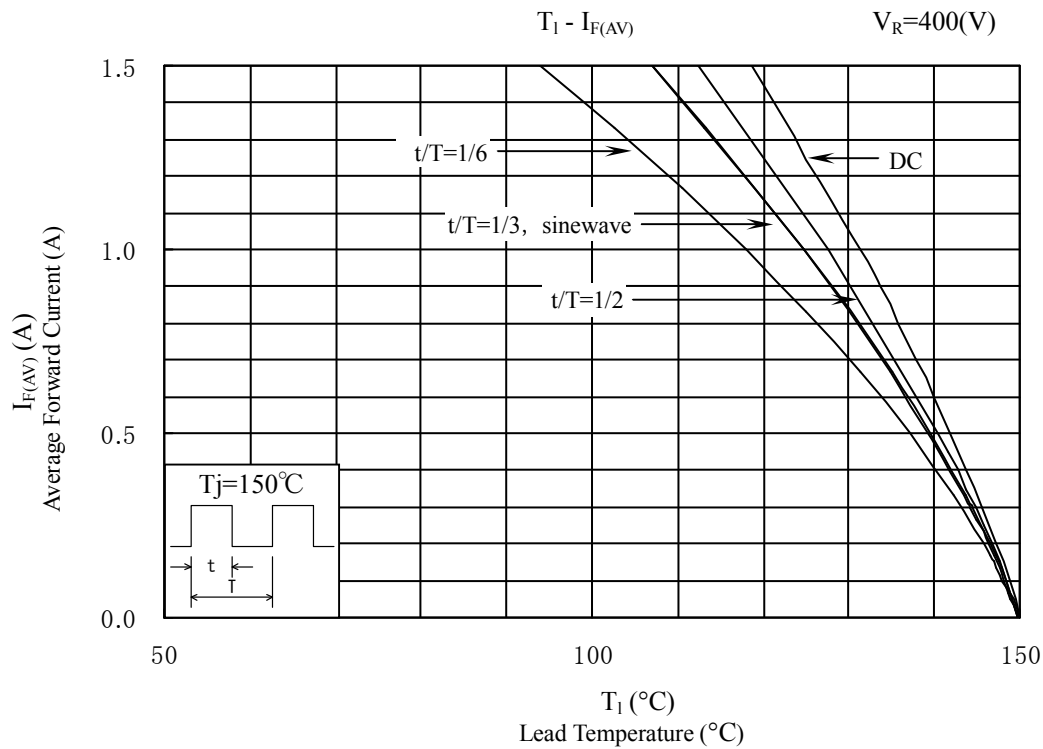
5 Electrical characteristics ($T_a=25^{\circ}C$, unless otherwise specified)

No.	Item	Symbol	Unit	Value	Conditions
1	Forward Voltage Drop	V_F	V	1.3 max.	$I_F=1.5A$
2	Reverse Leakage Current	I_R	μA	10 max.	$V_R=V_{RM}$
3	Reverse Leakage Current Under High Temperature	$H \cdot I_R$	μA	50 max.	$V_R=V_{RM}, T_j=150^{\circ}C$
4	Reverse Recovery Time	trr-1	ns	50 max.	$I_F=I_{RP}=100mA$ 90% Recovery point, $T_j=25^{\circ}C$
		trr-2	ns	35 max.	$I_F=100mA, I_{RP}=200mA$ 75% Recovery point, $T_j=25^{\circ}C$
5	Thermal Resistance	$R_{th(j-l)}$	$^{\circ}C/W$	20 max.	Between Junction and lead

6 Characteristics

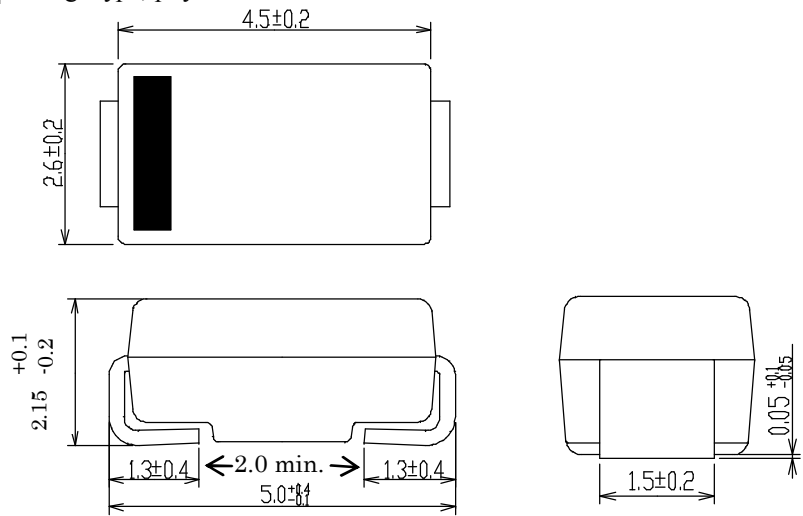


7 Derating



8 Package information

8-1 Package type, physical dimensions and material

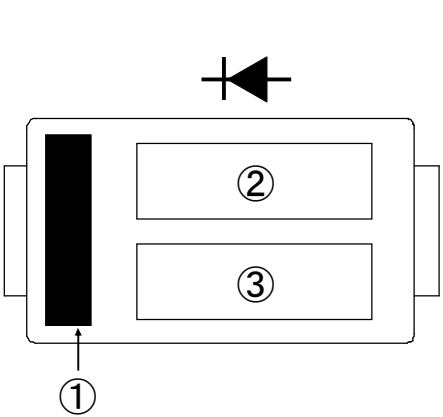


単位 : mm
Dimensions in mm

8-2 Appearance

The body shall be clean and shall not bear any stain, rust or flaw.

8-3 Marking



① Polarity marking (Cathode band)

② Type number
SJPL-F4 as abbreviated of LF4

③ Lot number
Example) 6D11
6: Last number of Year
D: Month from 1 to 9 for Jan. to Sep.
O for Oct., N for Nov., D for Dec.
11: Day